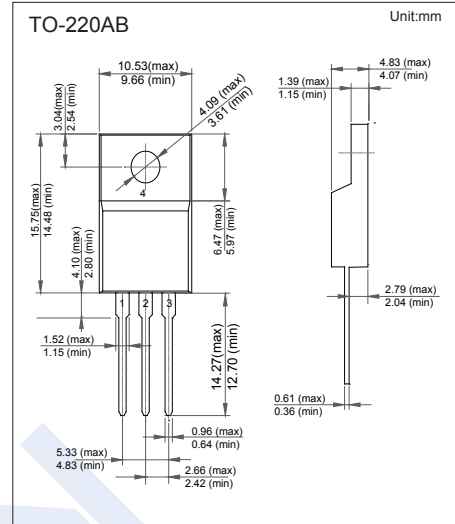
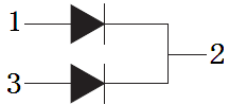


Schottky Diodes SBRF30100C

■ Features

- Common cathode structure
- Low power loss, high efficiency
- High Operating Junction Temperature
- High Operating Junction Temperature
- Guard ring for overvoltage protection, High reliability
- RoHS product



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Repetitive Peak Reverse Voltage	V_{RRM}	100	V
Maximum DC Blocking Voltage	V_{DC}	100	
Average Forward Current	I_{FAV}	30	A
Per Device		15	
Per Diode			
Surge Non-Repetitive Forward Current	I_{FSM}	275	
Thermal Resistance Junction to Case	$R_{\theta JC}$	1.8	°C/W
Junction Temperature	T_J	175	°C
Storage Temperature range	T_{stg}	-40 to 150	

■ Electrical Characteristics Ta = 25°C

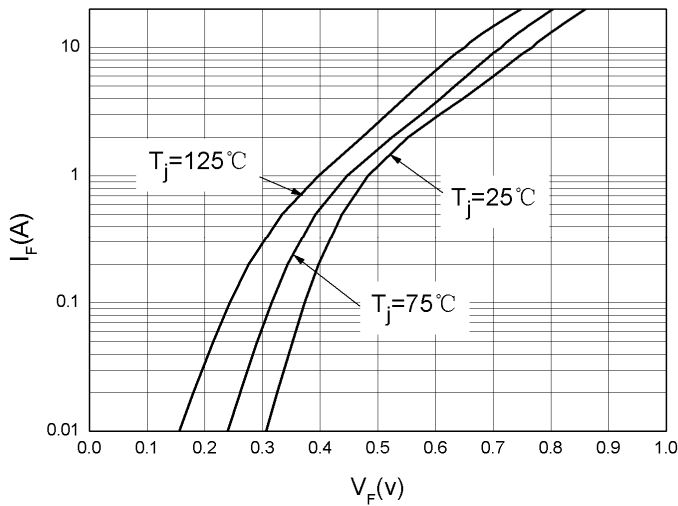
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Reverse breakdown voltage	V_R	$I_R = 100 \mu A$	100			V
Forward voltage	V_F	$I_F = 15 A, T_J = 25^\circ C$			0.9	
		$I_F = 15 A, T_J = 125^\circ C$			0.75	
Reverse voltage leakage current	I_R	$V_R = V_{RRM}, T_J = 25^\circ C$			30	μA
		$V_R = V_{RRM}, T_J = 125^\circ C$			30	mA

Schottky Diodes

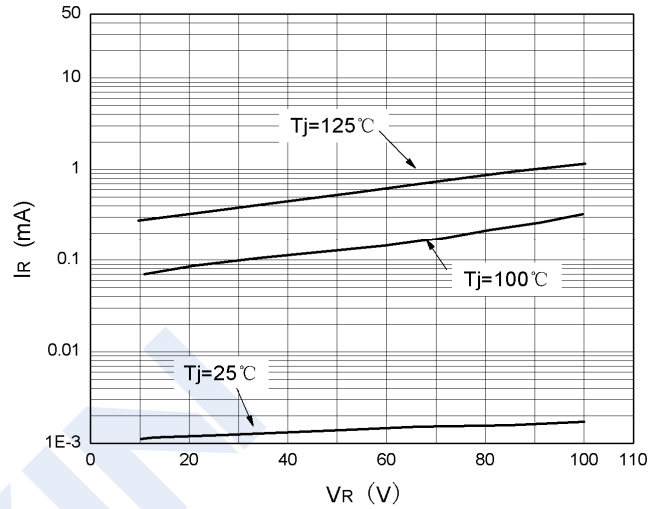
SBRF30100C

■ Typical Characteristics

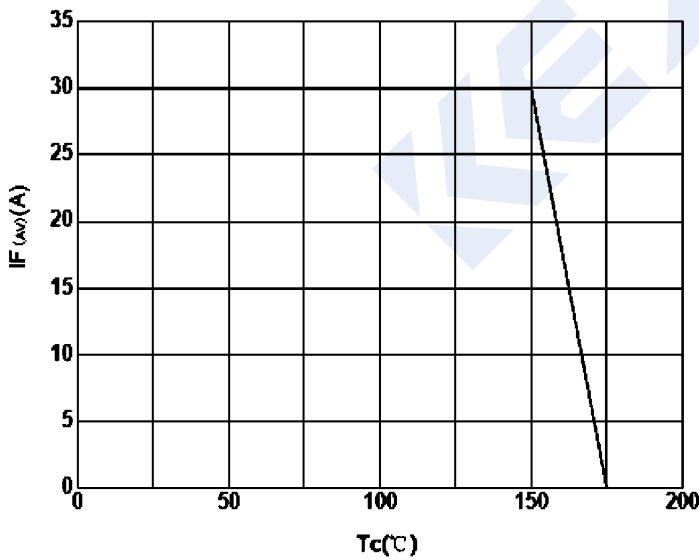
I_F vs V_F



I_R vs V_R



$I_F(AV)$ vs T_C



C_T vs V_R

